Amendments to the Claims

1. (Currently amended) A silicon epitaxial wafer ~~having an excellent gettering capability in the entire radial direction thereof~~, comprising a silicon single crystal substrate and an epitaxial layer grown on a surface of the silicon single crystal substrate, wherein the silicon single crystal substrate after epitaxial growth has a density of oxide precipitates which are detectable in the interior of ~~a~~ the silicon single crystal substrate ~~after epitaxial growth is~~ of $1\times10^9/cm^3$ or higher at any position in the radial direction, and wherein the silicon single crystal substrate prior to epitaxial growth is heat treated in an oxidizing atmosphere so that Grown-in precipitation nuclei are grown in the silicon single crystal but stacking faults in the form of a ring are not generated in the silicon single crystal substrate.

2. (Cancelled)

3. (Previously presented) The silicon epitaxial wafer according to claim 1, wherein the silicon single crystal substrate prior to the epitaxial growth is a boron-doped substrate having resistivity of 0.1 Ω·cm or lower.

4. (Currently amended) A process for manufacturing a silicon epitaxial wafer ~~having an excellent gettering capability in the entire substrate~~ comprising the steps of:

heat treating a silicon single crystal substrate in an oxidizing atmosphere ~~for a growing~~ to grow Grown-in precipitation nuclei in the silicon single crystal substrate; and thereafter,

performing epitaxial growth on the substrate,

wherein ~~there is used as the substrate a silicon single crystal wafer which has Grown-in precipitation nuclei formed in a growth step for silicon single crystal, and in which~~ stacking faults in the form of a ring are not generated in ~~a~~ the silicon single crystal substrate during the heat treatment ~~in an oxidizing atmosphere~~.

5. (Original) The process for manufacturing a silicon epitaxial wafer according to claim 4, wherein the substrate is a boron-doped substrate having resistivity of 0.1 Ω·cm or lower.

6. (Cancelled)